

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	17777	(plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:30
2	BRS	L2	23604	tetraethylorthosilicate or TEOS	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:31
3	BRS	L3	148555 0	trench or gap or plug	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
4	BRS	L4	138454 7	oxide or SiO	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
5	BRS	L5	404797 7	remov\$6 or etch\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	77933	MOSFET or "metal oxide semiconductor field effect"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
7	BRS	L7	11044	(remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
8	BRS	L8	1198	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
9	BRS	L9	628	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
10	BRS	L11	3334	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L12	1098	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
12	IS&R	L15	95	(438/269).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
13	IS&R	L16	1318	(438/424).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
14	IS&R	L17	1237	(438/689).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
15	BRS	L18	39208	wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	IS&R	L19	743	(438/633).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
17	IS&R	L21	683	(438/691).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
18	IS&R	L22	1977	(438/692).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
19	IS&R	L23	1749	(438/270).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
20	BRS	L10	130	(((((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)) and (MOSFET or "metal oxide semiconductor field effect"))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L13	223	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))) and (MOSFET or "metal oxide semiconductor field effect")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
22	IS&R	L14	2	("20020081817").PN.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
23	BRS	L20	168	(wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6)) near4 oxide near4 trench\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:29
24	BRS	L24	4728	teos and trench and semiconductor adj substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:30
25	BRS	L25	1374	dry adj etching and (teos and trench and semiconductor adj substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:30

	Type	L #	Hits	Search Text	DBs	Time Stamp
26	BRS	L26	649	25 and wet adj etching	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:30
27	BRS	L27	429	26 and bottom	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:31
28	BRS	L28	277	27 and sidewalls	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/10/28 08:34
29	BRS	L31	0	20010031540.URPN.	USPAT	2004/10/28 08:35